Type	Hits	Search Text	DBs	Time Stamp
BRS	2645	semiconductor near inspection	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/9/04
BRS	1305	S1 and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/9/04
BRS	1	S2 and (virtual near wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/9/04
BRS	78	(virtual near wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/9/04
BRS	1	S4 and (die near inspection)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/9/04
BRS	617	(cell near rate)and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/9/04
BRS	1	S6 and S4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/9/04
BRS	114	wafer near inspecting near method	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/9/04
BRS	1	S8 and (virtual near cells)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/9/04
BRS	1	S8 and (virtual same cells)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/9/04
BRS	2	S8 and (virtual and cells)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/9/04
BRS	1749	(702/35 or 702/36 or 702/182 or 702/189).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/9/04
BRS	2943	(235/454 or 235/464 or 235/494).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/9/04
BRS	785	(382/144 or 382/145).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/9/04
BRS	298	(718/1).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/9/04
BRS	1697	(250/306).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/9/04
BRS	6687	S13 or S14 or S16 or S17	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/9/04
BRS	2645	semiconductor near inspection	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/9/04
BRS	1305	S22 and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/9/04
BRS	78	(virtual near wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/9/04
BRS	617	(cell near rate)and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/9/04
BRS	114	wafer near inspecting near method	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/9/04
BRS	1749	(702/35 or 702/36 or 702/182 or 702/189).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/9/04
BRS	2943	(235/454 or 235/464 or 235/494).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/9/04
BRS	785	(382/144 or 382/145).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/9/04
BRS	298	(718/1).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/9/04
BRS	1697	(250/306).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/9/04
BRS	6687	S33 or S34 or S36 or S37	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/9/04
BRS	1	S23 and (virtual near wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/9/04
BRS	1	S25 and (die near inspection)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/9/04
BRS	1	S27 and S25	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/9/04
BRS	1	S29 and (virtual near cells)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/9/04
BRS	1	S29 and (virtual same cells)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/9/04
BRS	2	S29 and (virtual and cells)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/9/04
BRS	38	S38 and S22	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/9/04
BRS	35	S39 and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/9/04
BRS	3	S40 and virtual	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/9/04
IS&R	90	(("5351197") or ("5914504") or ("5920088") or ("5963800") or ("5886376") or ("5960265") or ("6084229") or ("3896482") or ("4295149") or ("4422161") or ("4494069") or ("4524280") or ("4531144") or ("4543646") or ("4607219") or ("4610077") or ("4786613") or ("4823136") or ("4824489") or ("4824496") or ("4894114") or ("4904831") or ("4924287") or ("4963500") or ("4970686") or ("5016080") or ("5021856") or ("5051917") or ("5210046") or ("5217907") or ("5217916") or ("5221865") or ("5256274") or ("5281545") or ("5283203") or ("5345417") or ("5350704") or ("5357472") or ("5368711") or ("5369595") or ("5369596") or ("5372649") or ("5387810") or ("5388054") or ("5440153") or ("5451801") or ("5459340") or ("5534798") or ("5566877") or ("5671234")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/10/04
BRS	63	S42 and (semiconductor and wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/10/04
BRS	10	S43 and inspection	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/10/04
BRS	28	S43 and (inspection or test)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/10/04
BRS	7	S45 and (virtual or simulated)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/10/04
BRS	6	S46 and cell$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/10/04
BRS	6	S47 and standard	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/10/04
BRS	4877	(235/375 or 235/376 or 235/385).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/10/04
BRS	1	S49 and (inspect$3 near semiconductor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/10/04
BRS	2645	semiconductor near inspection	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/10/04
IS&R	7	("20020109088").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/10/04
IS&R	2	("6415977").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	11/10/04